

WEST**Freeform Search**

Database: US Patents Full-Text Database ▲
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Derwent World Patents Index
IBM Technical Disclosure Bulletins ▼

Term: 17 and (octafluorocyclobutane or "c.sub.4 F.sub.8" or perfluoropropylene or "C.sub.3 F.sub.6") ▲
▼

Display: 25 **Documents in Display Format:** CIT **Starting with Number** 1

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Search History

Today's Date: 12/11/2001

<u>DB Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
USPT,PGPB	17 and (octafluorocyclobutane or "c.sub.4 F.sub.8" or perfluoropropylene or "C.sub.3 F.sub.6")	3	<u>L9</u>
USPT,PGPB	I6 same I7	5	<u>L8</u>
USPT,PGPB	trench same (side wall near4 polymer)	11	<u>L7</u>
USPT,PGPB	silicon same etch\$3	50168	<u>L6</u>
USPT,PGPB	I3 and (trench same side wall protect\$3)	0	<u>L5</u>
USPT,PGPB	I1 and I2	269	<u>L4</u>
USPT,PGPB	I1 same I2	88	<u>L3</u>
USPT,PGPB	silicon same (etch\$3 selectivity or etch\$3 stop)	4950	<u>L2</u>
USPT,PGPB	(potassium hydroxide or "KOH") same oxide	10960	<u>L1</u>

	L #	Hits	Search Text	DBs	Time Stamp
1	L1	9135	silicon same trench	USPAT ; US-PG PUB	2001/12/1 1 10:21
2	L2	6201	1 same etch\$3	USPAT ; US-PG PUB	2001/12/1 1 10:22
3	L3	621	(separat\$3 adj layer) same etch\$3	USPAT ; US-PG PUB	2001/12/1 1 10:35
4	L4	64	12 and 13	USPAT ; US-PG PUB	2001/12/1 1 10:45
5	L5	2	4 and sensor	USPAT ; US-PG PUB	2001/12/1 1 10:46